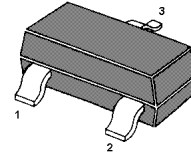


MMBTA06

NPN Silicon Epitaxial Planar Transistor

For switching and amplifier applications



1. Base 2. Emitter 3. Collector
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	80	V
Collector Emitter Voltage	V_{CEO}	80	V
Emitter Base Voltage	V_{EBO}	4	V
Collector Current	I_C	500	mA
Power Dissipation	P_{tot}	350	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 1\text{ V}$, $I_C = 10\text{ mA}$ at $V_{CE} = 1\text{ V}$, $I_C = 100\text{ mA}$	h_{FE} h_{FE}	100 100	- -	- -
Collector Base Cutoff Current at $V_{CB} = 80\text{ V}$	I_{CBO}	-	100	nA
Collector Emitter Cutoff Current at $V_{CE} = 60\text{ V}$	I_{CES}	-	100	nA
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	80	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	80	-	V
Emitter Base Breakdown Voltage at $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EBO}$	4	-	V
Collector Emitter Saturation Voltage at $I_C = 100\text{ mA}$, $I_B = 10\text{ mA}$	$V_{CE(sat)}$	-	0.25	V
Base Emitter On Voltage at $V_{CE} = 1\text{ V}$, $I_C = 100\text{ mA}$	$V_{BE(on)}$	-	1.2	V
Gain Bandwidth Product at $I_C = 10\text{ mA}$, $V_{CE} = 2\text{ V}$, $f = 100\text{ MHz}$	f_T	100	-	MHz

